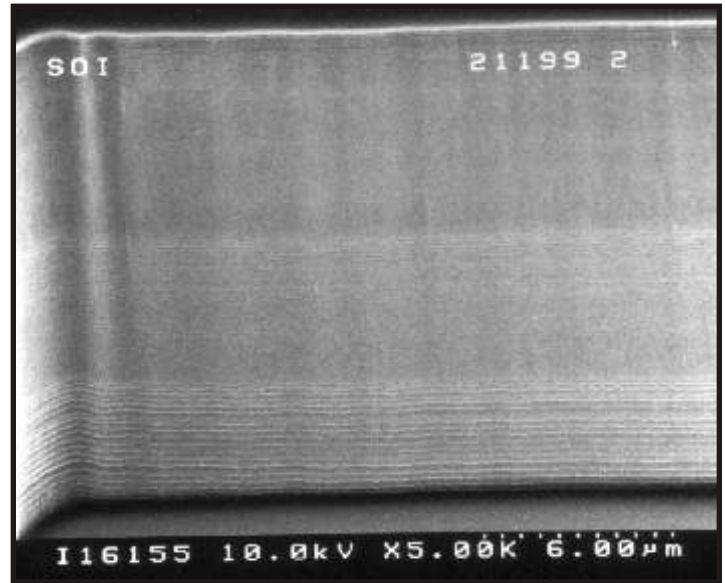
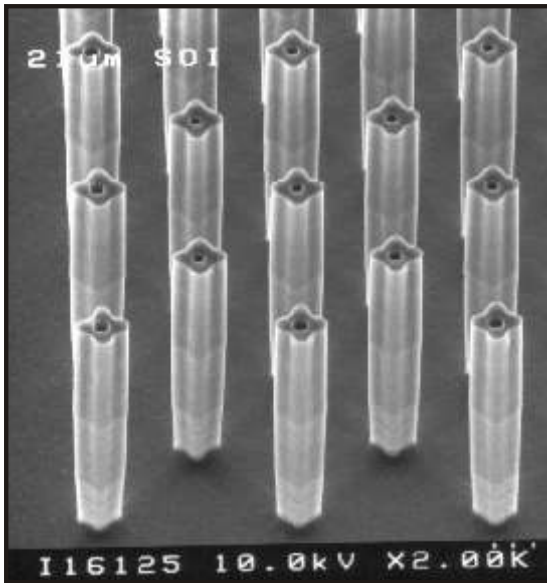


Plasmalab Data

Si ICP Etching for SOI technology



21 µm deep anisotropic etch stopping on SiO₂
(SEM's supplied by an OPT user)

Results:

Rate : 1µm/ min by ICP180
Rates up to 10 µm/ min are possible
with the larger ICP 380 source.
uniformity over 4" wafer ± 4% (ICP180)
selectivity to SiO₂ underneath > 100: 1

Plasmalab System 100
Plasmalab 80 Plus

Technology:

Reactive Ion Etching
with ICP Source (13.56 MHz)
Inductive Coupled Plasma
RF driven substrate electrode
substrate temperature control
Fluorine based 3 step process
gas chopping

